Preparation and Characterization of Transparent and Conductive SnO2 Thin Films by Spray Pyrolysis

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Abstract : Thin films of undoped and As-doped tin oxide (As:SnO2) were obtained on silicon and glass substrates at 450° - 480° C by spray pyrolysis technique. Tin chloride (SnCl4.5H2O) and As oxide (3As2O5.5H2O) were used as a source for Sn and As respectively. The As2O5 concentration was varied from 0 to 10 mol% in the starting water-alcoholic solution. The characterization of the films was provided with XRD, CEM, AFM and UV-VIS spectroscopy. The influence of the synthesis parameters (the temperature of the substrate, solution concentration, gas and solution flow rates, deposition time, nozzle-to substrate distance) on the optical, electrical and structural properties of the films. Films grown at low temperatures (<300°C) are amorphous whereas this deposited at higher temperatures have certain degree of polycrystallinity. Thin oxide films deposited at 450°C are generally polycrystalline with tetragonal rutile structure. The resistivity decreases with dopant concentration. The minimum resistivity smaller than 7.5.10-4 Ω .cm were achieved in the films deposited at 480°C. The As doped films (SnO2: As) deposited on silicon substrates was used for preparation of a large area position sensitive photodetector (PSD), acting on the base of a lateral photovoltaic effect. The position characteristic of PSD is symmetric to the zero and linear in the 80% of the active area. The SnO2 films are extremely stable under typical environmental conditions and extremely resistant to chemical etching.

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